



Coating Uniformity & Litho Performance of AZ[®] 15nXT (450cSt) @ FT = 15, 20, 35 μm

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Coat Parameters on 200 mm Wafers

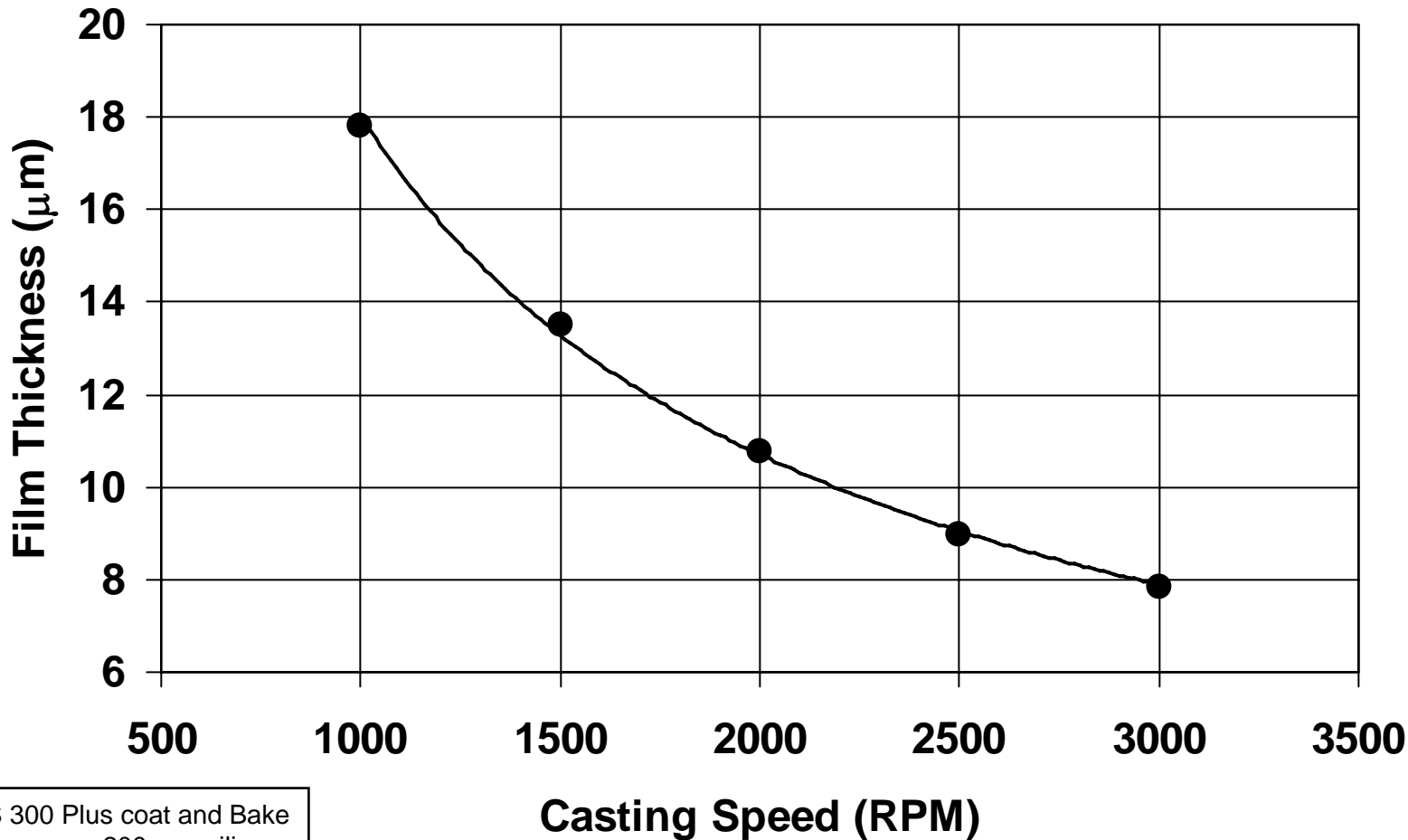
AZ[®] 15nXT (450cSt)

Suss MicroTec ACS 300 Plus: Coater <no EBR 20 um, 15nXT-N2 200 mm>							
Step	Time	Speed	Accel	Function	Exhaust	Exhaust +/-	Coverplate
	(s)	(rpm)	(rpm)		(l/min)	(l/min)	(mm)
1	2	100	2000		1500	300	140
2	15	30	2000	Dispense resist	1500	300	140
3	3	300	2000	Resist expanding on wafer	1500	300	140
4	1.5	1600	2000	Quick Spin	1500	300	140
5	15	xxx	2000	Main Spin/Backside Rinse	1500	300	140
6	15	400	2000	Backside Rinse	1500	300	140
7	15	400	2000		1500	300	140
8	0.5	1300	4000		1500	300	140
9	1	0	4000		1500	300	140

Suss MicroTec ACS 300 Plus:		
Baking Temperature 120 °C/3min		
Step	Time	Proximity
	(s)	(mm)
1	20	5.1
2	20	1.5
3	60	0.1
4	120	0

AZ[®] 15nXT (450cSt), Lot# 2518-134

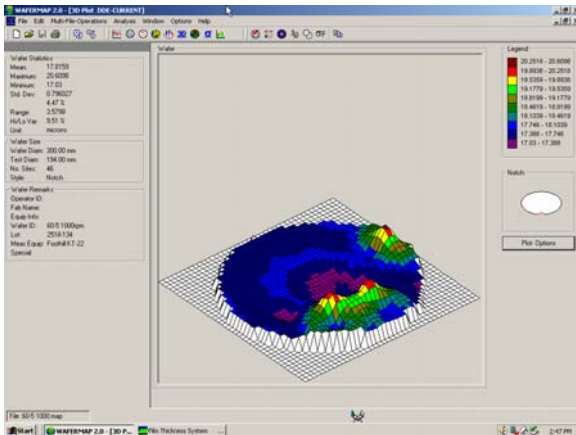
Spin Curve On 200 mm Si Wafers



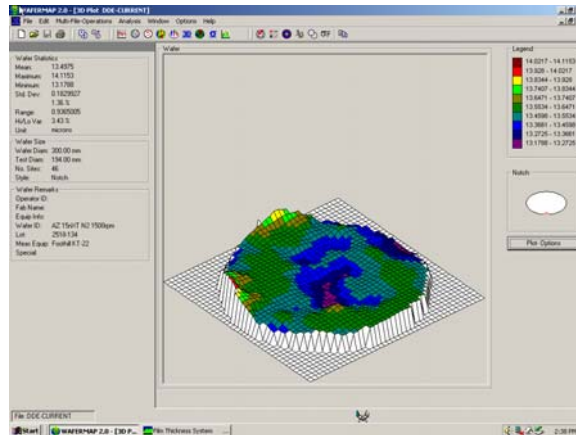
Suss ACS 300 Plus coat and Bake
Hand dispense on 200 mm silicon
Spin 1000-3000 rpm for 15 sec
SB: 120°C/ 3 minutes

AZ[®] 15nXT (450cSt) Wafer Uniformity Maps (3mm Edge Exclusion)

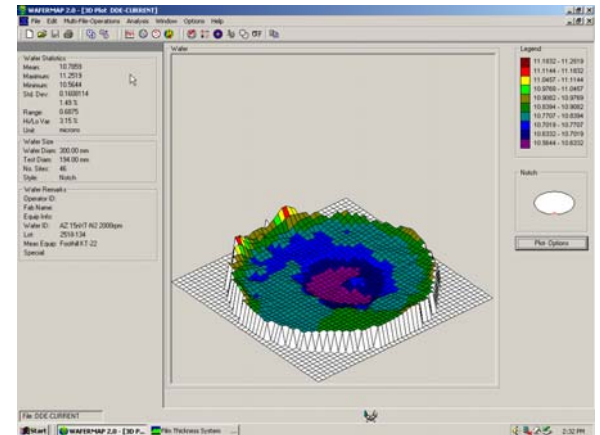
1000 rpm 17.8 μ m/4.49%RSD



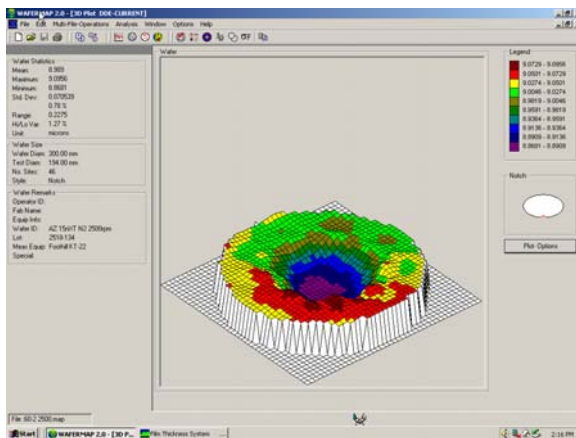
1500 rpm 13.5 μ m/1.36%RSD



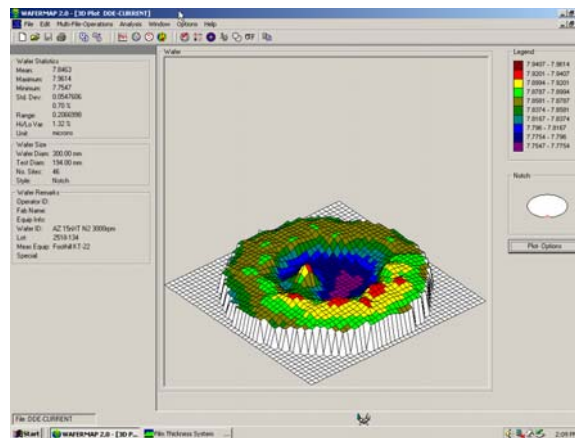
2000 rpm 10.8 μ m/1.49%RSD



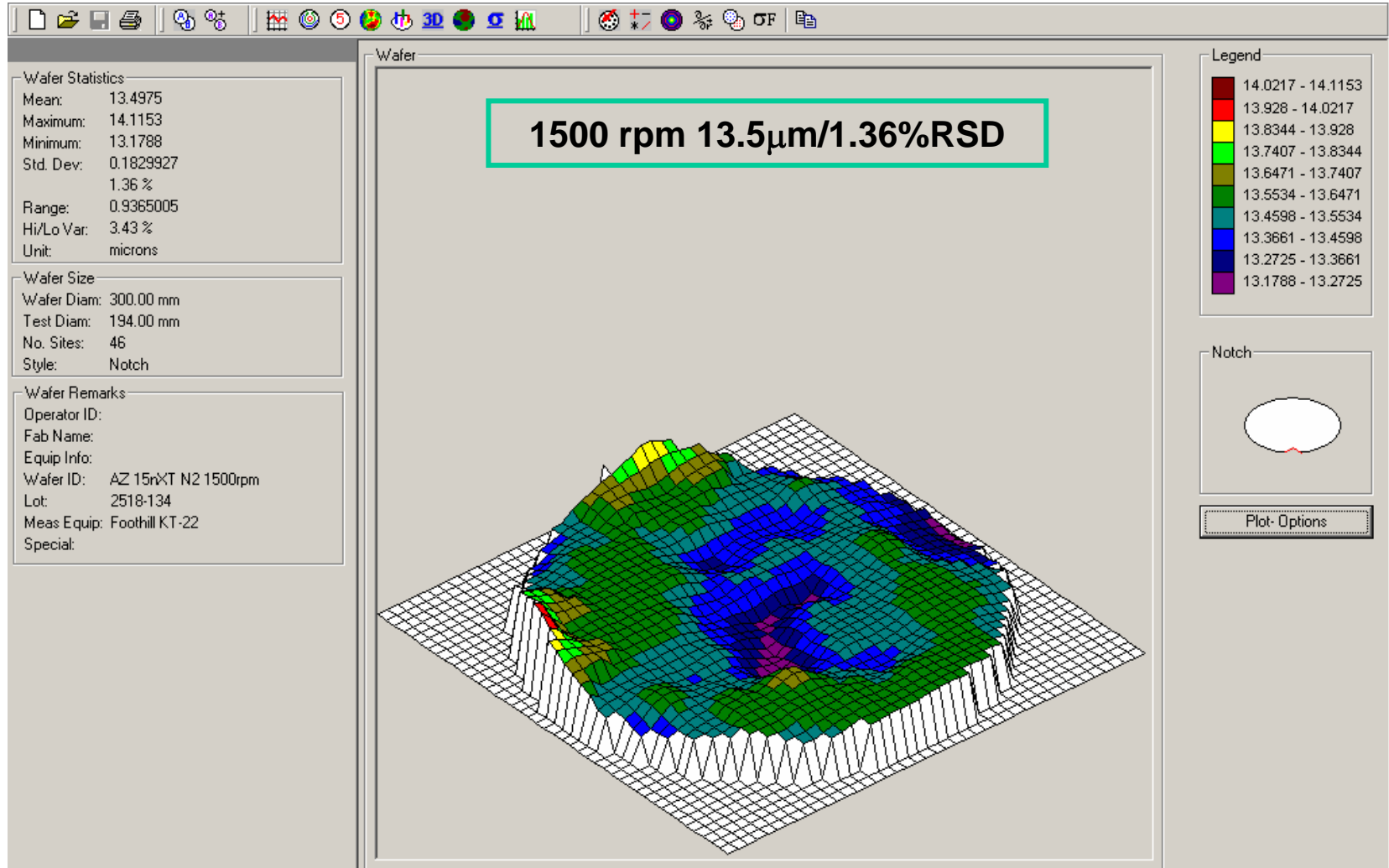
2500 rpm 9.0 μ m/0.78%RSD



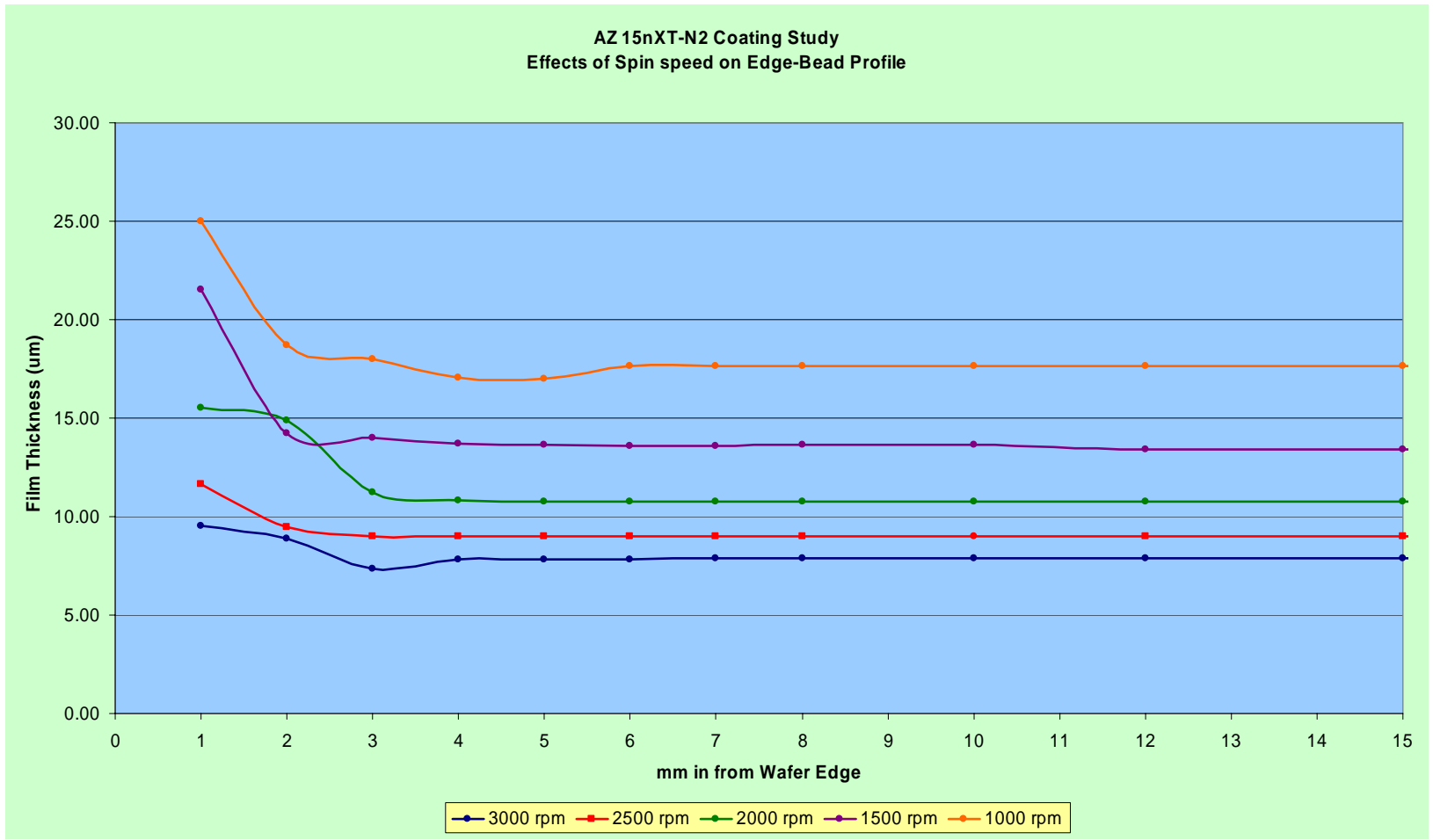
3000 rpm 7.8 μ m/0.70%RSD



AZ[®] 15nXT (450cSt) Wafer Uniformity Maps (3mm Edge Exclusion)



AZ[®] 15nXT (450cSt), Edge-Bead Coating Study 200mm wafer



Process Conditions

Substrate: Si and Cu wafer

Resist: AZ[®] 15nXT (450cSt), 2518-134

Process Condition:

FT=15 μm by single coat (Cu)	SB 120 °C/3 minutes
FT=20 mm by single coat (Cu)	SB 120 °C/4 minutes
FT=35 mm by single coat (Si)	SB 120 °C/5 minutes

Exposure tool: Suss (g-h-i-line); plating mask

FT= 15 & 20 μm **Dose:** 1200, 1100, 1000, 900, 800

FT= 35 μm **Dose:** 1400, 1200, 1000, 800

PEB: 120 °C/1 min

Development: AZ 300 MIF

FT= 15 μm 3x50 puddles

FT= 20 μm 4x50 puddles

FT= 35 μm 5x50 puddles

**Resolution
Solid Line
on Cu**

**FT = 15 μm
900 mJ/cm^2**

**FT = 20 μm
1000 mJ/cm^2**

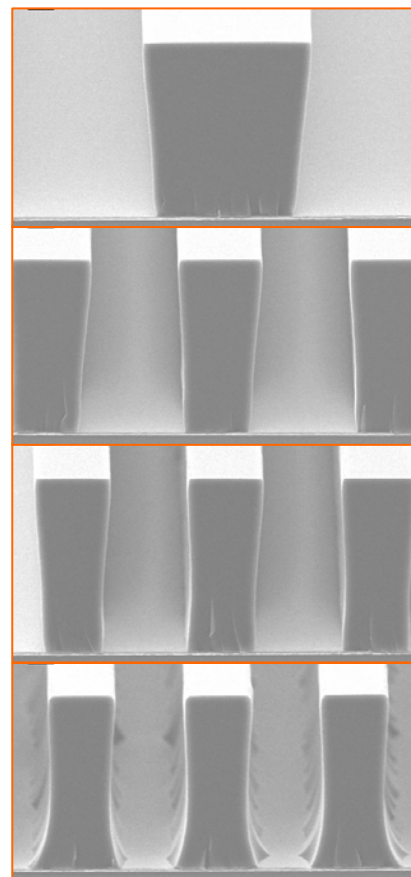
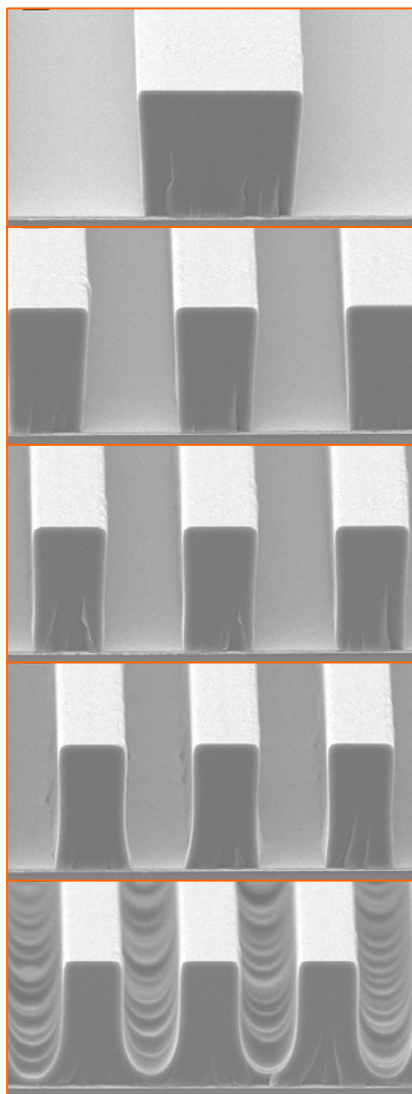
20 μm

10 μm

9 μm

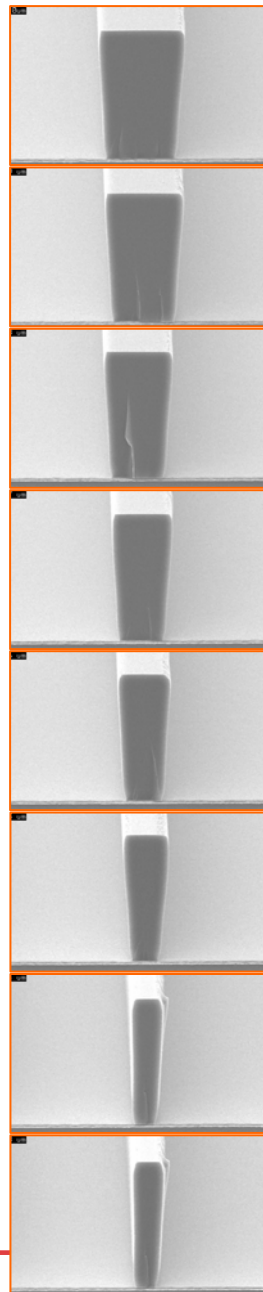
8 μm

7 μm



Isolated Line on Cu

**FT = 15 μm
900 mJ/cm^2**



10 μm

9 μm

8 μm

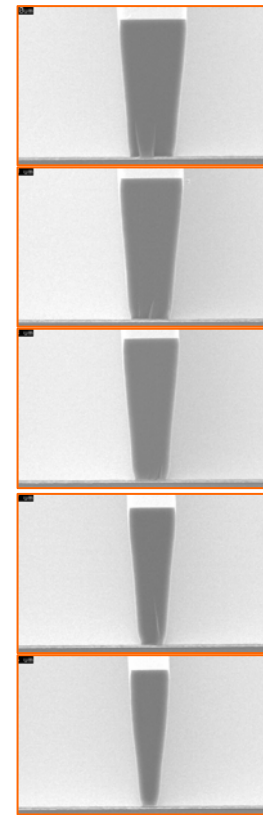
7 μm

6 μm

5 μm

4 μm

3 μm



**FT = 20 μm
1000 mJ/cm^2**

Exposure latitude on Cu

FT = 15 μm
CD 10 μm

FT = 20 μm
CD 10 μm

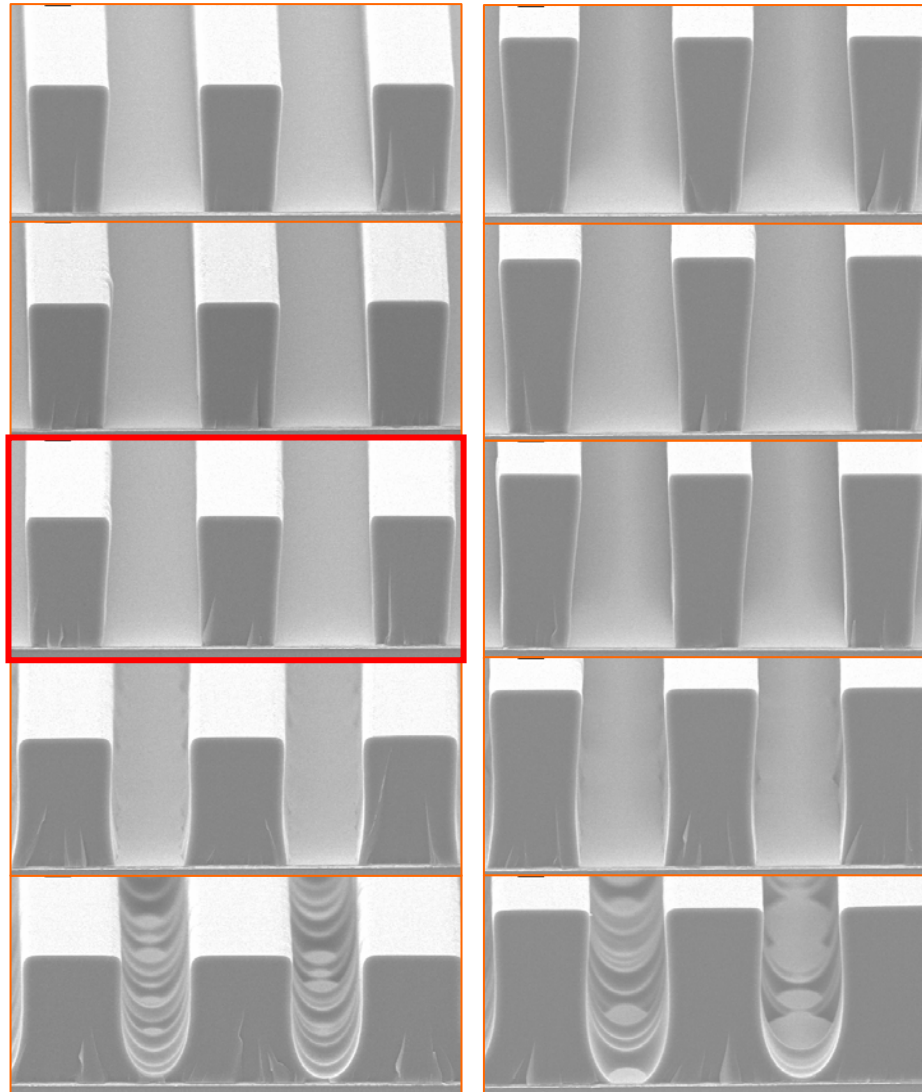
800
 mJ/cm^2

900
 mJ/cm^2

1000
 mJ/cm^2

1100
 mJ/cm^2

1200
 mJ/cm^2



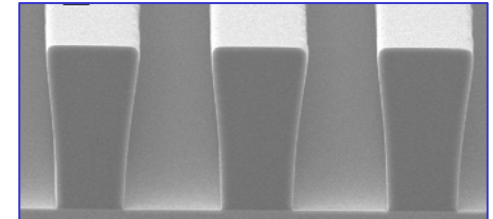
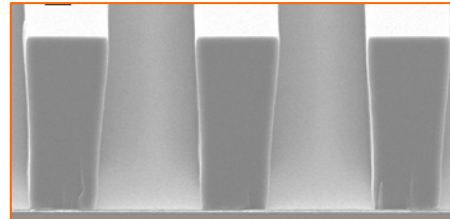
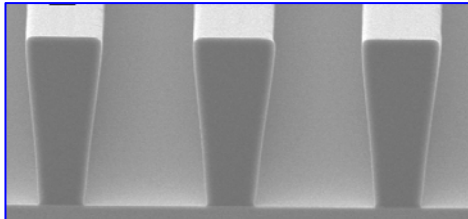
**FT = 20 μm
CD 10 μm**

**SB:120°C/4 min
Develop: 4x60**

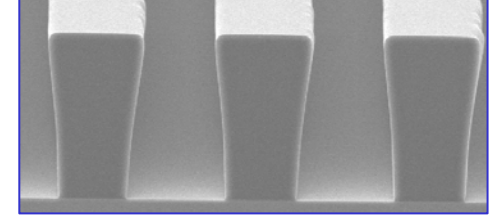
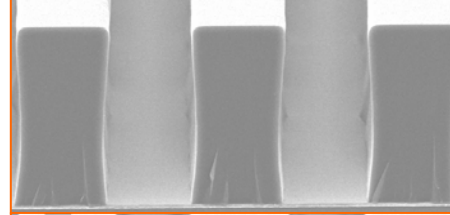
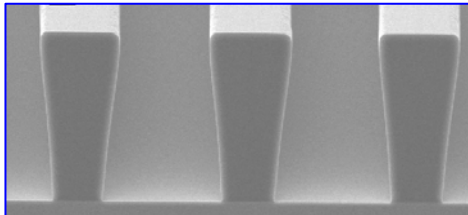
**SB:120°C/4 min
Develop: 4x50**

**SB:110 °C/4 min
Develop:4x60**

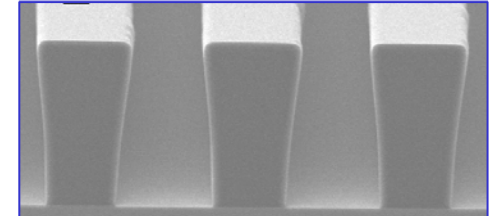
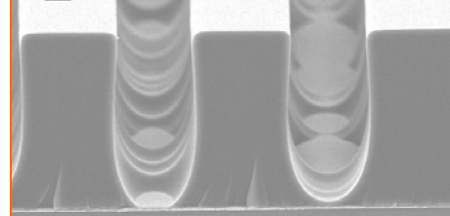
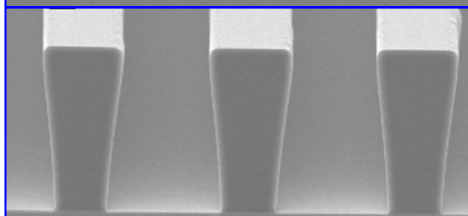
1000
 mJ/cm^2



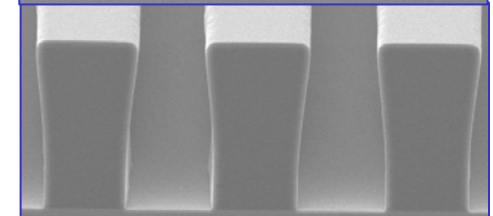
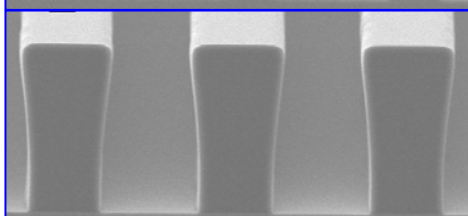
1100
 mJ/cm^2



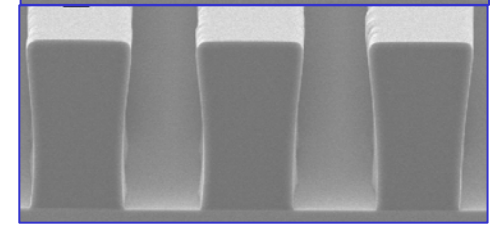
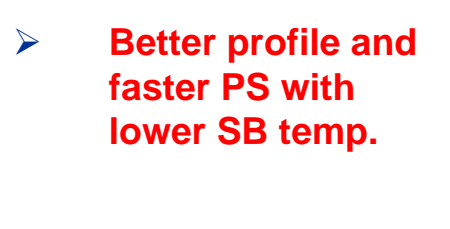
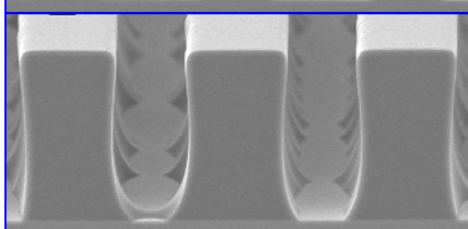
1200
 mJ/cm^2



1300
 mJ/cm^2



1400
 mJ/cm^2



- **More converted profile with longer development time.**
- **Better profile and faster PS with lower SB temp.**

**Resolution
Solid Line
on Si**

**FT = 35 μm
1400 mJ/cm²**

**FT = 35 μm
1200 mJ/cm²**

50 μm

40 μm

30 μm

20 μm

10 μm

